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FORM PTO-1449 (Rev. 5/92)	SAMUELS, GAUTHIER & STEVENS LLP 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180	ATTORNEY DOCKET NO. MIT9889 <u>Lee et al.</u> APPLICANT: <u>Herewith</u> FILING DATE: <u>6/25/03</u>	SERIAL NO. Unknown <u>10/603 712</u> GROUP: Unknown <u>2015</u> EXAMINER: Unknown <u>A. Wilson</u>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
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	AJ						
	AK						
	AL						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
<u>Ole</u>	AM	"Characteristics and Device Design of Sun-100nm Strained Si N- and PMOSFETs"; Rim et al., 2002 Symposium on VLSI Technology Digest of Technical Papers
<u>Ole</u>	AN	"Hole mobility enhancements and alloy scattering-limited mobility in tensile strained Se/SiGe surface channel metal-oxide-semiconductor field-effect transistors: Leitz et al., Journal of Applied Physics, Vol. 92, No. 7; October 1, 2002; pgs: 3745-3751
	AO	

EXAMINER B. Madsen DATE CONSIDERED 7/30/04

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10/603,712
SERIAL NO.

APPLICANT: Lee et al.

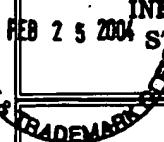
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FILING DATE: 06/25/2003

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>One</i>	AA	2002/0052084	05/02/2002	Fitzgerald			05/02/2002
	AB						
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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AE						
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	AH						

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EXAMINER INITIAL		
<i>One</i>	AI	"Channel width dependence of mobility in Ge channel modulation-doped structures;" Irisawa et al. <i>Jpn. J. Appl. Phys.</i> April 2001. Vol. 40.
	AJ	"Thermal stability of Ge channel modulation doped structures," Irisawa et al. <i>Journal of Crystal Growth</i> . 2001. Vol. 227-228.
	AK	"Hall mobility enhancement caused by annealing of $Si_{0.2}Ge_{0.8}/Si_{0.7}Ge_{0.3}/Si(001)$ p-type modulation-doped heterostructures," Myronov et al. <i>Applied Physics Letters</i> . May 2002. Vol. 80, No. 19.
	AL	"Quantum mechanical modeling of the charge distribution in a $Si/Si_{1-x}Ge_x/Si$ P-Channel MOSFET," Hargrove et al. <i>Proceedings of the 1994 IEEE International Electron Devices Meeting</i> , San Francisco, CA. December 1994.
	AM	"Characteristics and device design of Sub-100 nm strained Si N- and PMOSFETs," Rim et al. <i>Symposium on VLSI Technology Digest of Technical Papers</i> . 2002.
	AN	"Enhanced performance of strained-Si MOSFETs on CMP SiGe Virtual Substrate," Sugii et al. <i>International Electron Devices Meeting 2001</i> . IEDM. Technical Digest.
	AO	"SiGe-On-Insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation," Cheng et al. <i>IEEE International SOI Conference</i> . Durango, CO. October 2001.
<i>One</i>	AP	"Ultrahigh room-temperature hole hall and effective mobility in $Si_{0.3}Ge_{0.7}/Ge/Si_{0.3}Ge_{0.7}$ heterostructures," Irisawa et al. <i>Applied Physics Letters</i> . July 2002. Vol. 81, No. 5.

EXAMINER *A. Wilson* DATE CONSIDERED *9/30/04*

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